

New Jersey Semi-Conductor Products, Inc.

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1N5614 S2M
1N5616 S4M
1N5618 S6M
1N5620 S8M
1N5622 S0M

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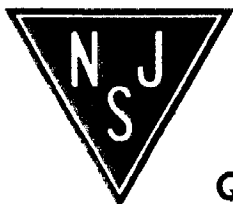
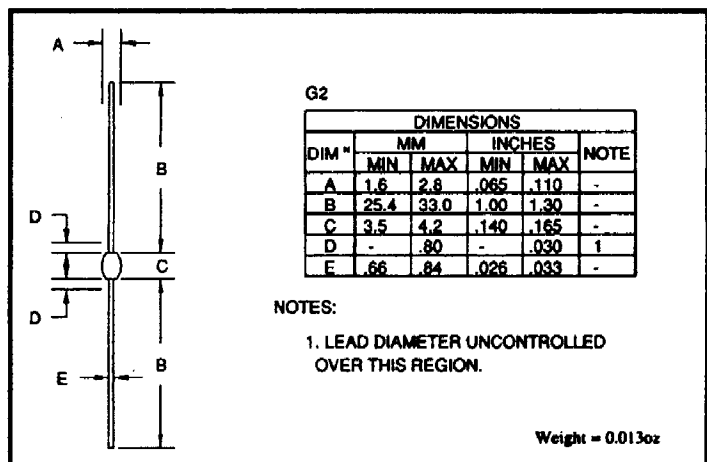
QUICK REFERENCE DATA AXIAL LEADED HERMETICALLY SEALED STANDARD RECOVERY RECTIFIER DIODE

- $V_R = 200 - 1000V$
- $I_F = 2.0A$
- $t_{rr} = 2\mu S$
- $V_F = 1.1V$
- Low reverse leakage current
- Hermetically sealed in Metoxillite fused metal oxide
- Good thermal shock resistance
- Low forward voltage drop
- Avalanche capability.

ABSOLUTE MAXIMUM RATINGS (@ 25°C unless otherwise specified)

	Symbol	1N5614	1N5616	1N5618	1N5620	1N5622	Unit
		S2M	S4M	S6M	S8M	S0M	
Working reverse voltage	V_{RWM}	200	400	600	800	1000	V
Repetitive reverse voltage	V_{RRM}	200	400	600	800	1000	V
Average forward current (@ 55°C, lead length 0.375")	$I_{F(AV)}$	←————— 2.0 —————→					A
Repetitive surge current (@ 55°C in free air, lead length 0.375")	I_{FRM}	←————— 10 —————→					A
Non-repetitive surge current ($t_p = 8.3mS$, @ V_R & T_{jmax})	I_{FSM}	←————— 30 —————→					A
Storage temperature range	T_{STG}	←————— -65 to +175 —————→					°C
Operating temperature range	T_{OP}	←————— -65 to +175 —————→					°C

MECHANICAL



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

CHARACTERISTICS (@ 25°C unless otherwise specified)

	Symbol	1N5614	1N5616	1N5618	1N5620	1N5622	Unit
		S2M	S4M	S6M	S8M	S0M	
Average forward current (sine wave) - max. pcb mounted; $T_A = 55^\circ\text{C}$ - max. $L = 3/8"$; $T_L = 55^\circ\text{C}$	$I_{F(AV)}$	←———— 1.0 —————→					A
	$I_{F(AV)}$	←———— 2.0 —————→					A
I^2t for fusing ($t = 8.3\text{mS}$) max.	I^2t	←———— 5.0 —————→					A^2S
Forward voltage drop max. @ $I_F = 1.0\text{A}$, $T_j = 25^\circ\text{C}$	V_F	←———— 1.1 —————→					V
Reverse current max. @ V_{RWM} , $T_j = 25^\circ\text{C}$	I_R	←———— 0.5 —————→					μA
@ V_{RWM} , $T_j = 100^\circ\text{C}$	I_R	←———— 25 —————→					μA
Reverse recovery time max. 0.5A I_F to 1.0A I_R . Recovers to 0.25A I_{RR} .	t_{rr}	←———— 2.0 —————→					μS
Junction capacitance typ. @ $V_R = 5\text{V}$, $f = 1\text{MHz}$	C_j	←———— 23 —————→					pF
Thermal resistance - junction to lead Lead length = 0.375"	$R_{\theta JL}$	←———— 38 —————→					$^\circ\text{C/W}$
Lead length = 0"	$R_{\theta JL}$	←———— 7 —————→					$^\circ\text{C/W}$
Thermal resistance - junction to amb. on 0.06" thick pcb. 1 oz. copper.	$R_{\theta JA}$	←———— 95 —————→					$^\circ\text{C/W}$

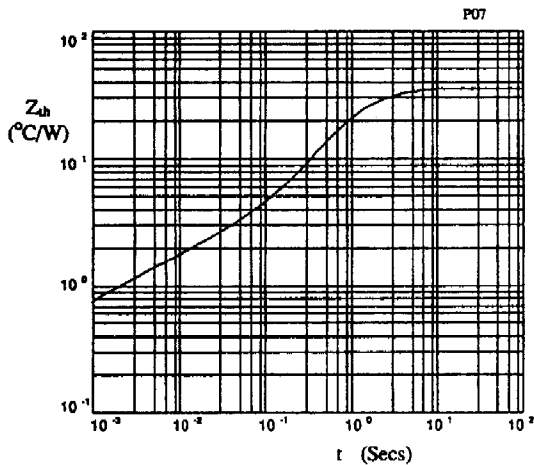


Fig 1. Transient thermal impedance characteristic.

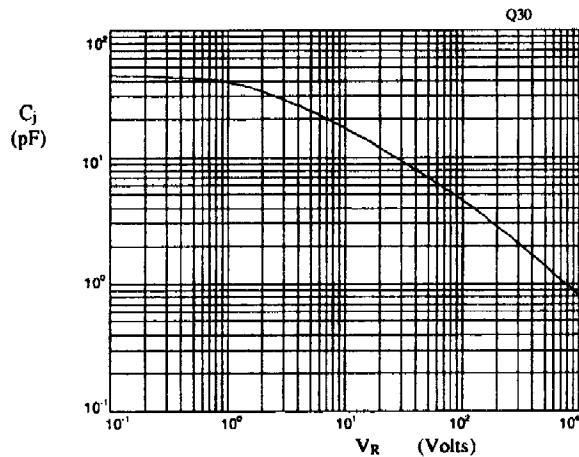


Fig 2. Typical junction capacitance as a function of reverse voltage.